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TRADE MARK

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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
TH	6.	Fayolle et al.; "Integration of Cu/SiOC in Dual Damascene Interconnect for 0.1µm technology using a new SiC material as dielectric barrier" 2002 IEEE International Interconnect Technology Conference, Burlingame, CA 39-41 (2002).	
	7.	Gelatos et al.; "The Properties of a Plasma Deposited Candidate Insulator for Future Multilevel Interconnects Technology" Mat. Res. Soc. Symp. 250 347-354 (1992).	
	8.	Levy et al. "Evaluation of LPCVD Boron Nitride as a Low Dielectric Constant Material" Mat. Res. Soc. Symp. 427 469-478 (1996).	
	9.	Martin et al.; "Integration of SiCN as a Low κ Etch Stop and Cu Passivation in a High Performance Cu/Low κ Interconnect" 2002 IEEE International Interconnect Technology Conference, Burlingame, CA 4244 (2002).	
	10.	Nguyen et al.; "Plasma-Assisted Chemical Vapor Deposition and Characterization of Boron Nitride Films" J. Electrochem. Soc., 141:6 1633-1638 (1994).	
TH	11.	Sugino et al.; "Dielectric constant of boron carbon nitride films synthesized by plasma-assisted chemical-vapor deposition" Applied Physics Letters 80:4 649-651 (2002).	

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Feb. 2006

Date Considered